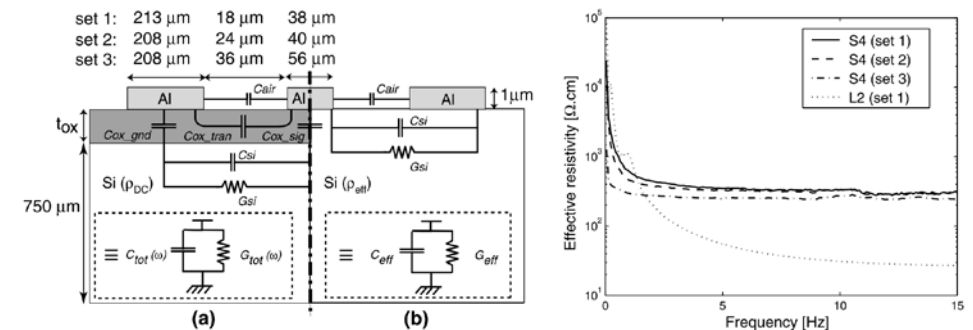


Investigation and characterisation of GaN-on-Silicon Technology for mm-wave application

Background

GaN-on-Silicon technology recently draws a lot of attraction due to its good RF/microwave performance and cost efficiency. However, the behaviour of such processes as well as substrates, e.g. high-resistivity silicon, need to be well investigated and characterised for high frequency. A CPW structure as an example is shown on the right hand side and the transmission-line parameters, e.g. permittivity, have to be extracted.



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Tasks

The tasks may involve :

- Paper survey
- Design of test keys
- Measurement and parameter extraction
- Data process

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